AUTOMOTIVE GRADE

Features

- Advanced Process Technology
- Low On-Resistance
- P-Channel MOSFET
- Dynamic dV/dT Rating

International

ICR Rectifier

- 150°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free, RoHS Compliant
- Automotive Qualified*

S III S IIII S III S IIII S III S II					
G TT 4 5 D					
Top View					

8 D	V _{(BR)DSS}	-30V
	R _{DS(on)} max.	0.02 Ω
	I _D	-10A

AUIRF7416Q

HEXFET[®] Power MOSFET

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_a) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ -10V	-10	
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ -10V	-7.1	А
I _{DM}	Pulsed Drain Current ①	-45	
P _D @T _A = 25°C	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	mW/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy [®]	370	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
ТJ	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range	-55 10 + 150	
Thermal Resist	ance	·	
	Parameter	Max.	Units
R _{eJA}	Junction-to-Ambient ^⑤	50	°C/W

	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-30		_		$V_{GS} = 0V, I_{D} = -250\mu A$
$\Delta V_{(BR)DSS} / \Delta T_J$	Breakdown Voltage Temp. Coefficient		-0.024		V/°C	Reference to 25° C, $I_{D} = -1$ mA
D	Static Drain-to-Source On-Resistance			0.020	Ω	V _{GS} = -10V, I _D = -5.6A ④
R _{DS(on)}	Static Drain-to-Source On-Resistance			0.035	52	V _{GS} = -4.5V, I _D = -2.8A ④
V _{GS(th)}	Gate Threshold Voltage	-1.0		-2.04	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
gfs	Forward Transconductance	5.6			S	V _{DS} = -10V, I _D = -2.8A
I _{DSS}	Drain-to-Source Leakage Current			-1.0		$V_{DS} = -24V, V_{GS} = 0V$
		_		-25	μA	$V_{DS} = -24V, V_{GS} = 0V, T_{J} = 125^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage			-100		V _{GS} = -20V
	Gate-to-Source Reverse Leakage			100	nA	V _{GS} = 20V

Static Electrical Characteristics @ $T_J = 25^{\circ}C$ (unless otherwise specified)

Dynamic Electrical Characteristics @ $T_J = 25^{\circ}C$ (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
Q _g	Total Gate Charge		61	92		I _D = -5.6A
Q _{gs}	Gate-to-Source Charge		8.0	12	nC	V _{DS} = -24V
Q _{gd}	Gate-to-Drain ("Miller") Charge		22	32		V _{GS} = -10V, See Fig. 6 & 9 ④
t _{d(on)}	Turn-On Delay Time		18			V _{DD} = -15V
t _r	Rise Time		49			I _D = -5.6A
t _{d(off)}	Turn-Off Delay Time		59		ns	$R_{G} = 6.2\Omega$
t _f	Fall Time		60			$R_D = 2.7\Omega$, See Fig. 10 ④
C _{iss}	Input Capacitance		1700			$V_{GS} = 0V$
C _{oss}	Output Capacitance		890		pF	V _{DS} = -25V
C _{rss}	Reverse Transfer Capacitance		410			f = 1.0MHz, See Fig. 5

Diode Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions
I _S	Continuous Source Current			-3.1		MOSFET symbol
	(Body Diode)			-3.1	А	showing the
I _{SM}	Pulsed Source Current			-45		integral reverse
	(Body Diode) ①			-45		p-n junction diode.
V_{SD}	Diode Forward Voltage			-1.0	V	T_J = 25°C, I_S = -5.6A, V_{GS} = 0V $③$
t _{rr}	Reverse Recovery Time		56	85		$T_{\rm J} = 25^{\circ} {\rm C}, {\rm I}_{\rm F} = -5.6{\rm A}$
Q _{rr}	Reverse Recovery Charge		99	150	nC	di/dt = 100A/µs

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

(a) Starting $T_J = 25^{\circ}C$, L = 25mH R_G = 25 Ω , I_{AS} = -5.6A. (See Figure 12)

- 3 I_{SD} \leq -5.6A, di/dt \leq 100A/µs, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150°C.
- ④ Pulse width \leq 300µs; duty cycle \leq 2%.
- ⑤ Surface mounted on FR-4 board, $t \le 10$ sec.

Qualification Information[†]

		Automotive (per AEC-Q101) ^{††}		
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.		
Moisture Sensitivity Level		SO-8 MSL1		
	Machine Model		Class M4 (+/- 425V) ^{†††} AEC-Q101-002	
ESD	Human Body Model		Class H1B (+/- 1000V) ^{†††} AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1125V) ^{†††} AEC-Q101-005		
RoHS Compliant		Yes		

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.











Fig 3. Typical Transfer Characteristics



Fig 4. Normalized On-Resistance Vs. Temperature



Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage



Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage



Fig 7. Typical Source-Drain Diode Forward Voltage



Fig 8. Maximum Safe Operating Area



Fig 9a. Basic Gate Charge Waveform





Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms



Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Fig 12a. Unclamped Inductive Test Circuit



Fig 12b. Unclamped Inductive Waveforms



Fig 12c. Maximum Avalanche Energy Vs. Drain Current

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements



*** V_{GS} = 5.0V for Logic Level and 3V Drive Devices

Fig 13. For P-Channel HEXFETS

International **IOR** Rectifier

SO-8 Package Outline

Dimensions are shown in millimeters (inches)





DIM	INC	HES	MILLIM	eters	
DIM	MIN	MAX	MIN	MAX	
Α	.0532	.0688	1.35	1.75	
A1	.0040	.0098	0.10	0.25	
b	.013	.020	0.33	0.51	
С	0075 .0098		0.19	0.25	
D	.189	.1968	4.80	5.00	
E	.1497	.1574	3.80	4.00	
е	.050 B	ASIC	1.27 BASIC		
e 1	.025 B	ASIC	0.635 E	35 BASIC	
Н	.2284	.2440	5.80	6.20	
K	.0099	.0196	0.25	0.50	
L	.016	.050	0.40	1.27	
у	0°	8°	0°	8°	



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: MILLIMETER
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- 5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
- (6) DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
- DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking



Note: For the most current drawing please refer to IR website at <u>http://www.irf.com/package/</u> www.irf.com



SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:

- CONTROLLING DIMENSION : MILLIMETER.
 ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
- 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.

2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF7416Q	SO-8	Tube	95	AUIRF7416Q
		Tape and Reel	2500	AUIRF7416QTR

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For technical support, please contact IR's Technical Assistance Center <u>http://www.irf.com/technical-info/</u>

> WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245 Tel: (310) 252-7105